

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX T <sub>C</sub> = +25°C
80V	25mΩ @ V <sub>GS</sub> = 10V	27A
	41mΩ @ V <sub>GS</sub> = 4.5V	21A

## Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMTH8028LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

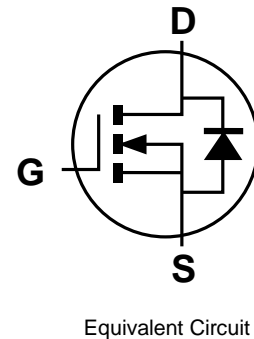
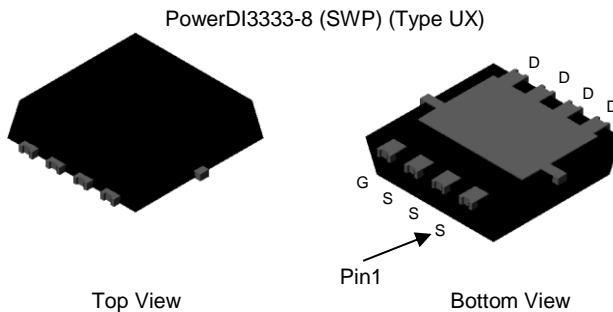
## Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

## Mechanical Data

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.072 grams (Approximate)

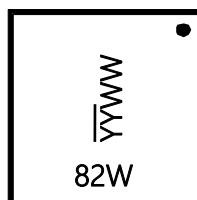


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8028LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape and Reel
DMTH8028LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape and Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



82W = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 21 = 2021)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	80	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	27
		T <sub>C</sub> = +100°C	19
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	108	A
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	27	A
Pulsed Body Diode Forward Current	I <sub>SM</sub>	108	A
Avalanche Current, L = 0.3mH (Note 8)	I <sub>AS</sub>	12.5	A
Avalanche Energy, L = 0.3mH (Note 8)	E <sub>AS</sub>	23.4	mJ

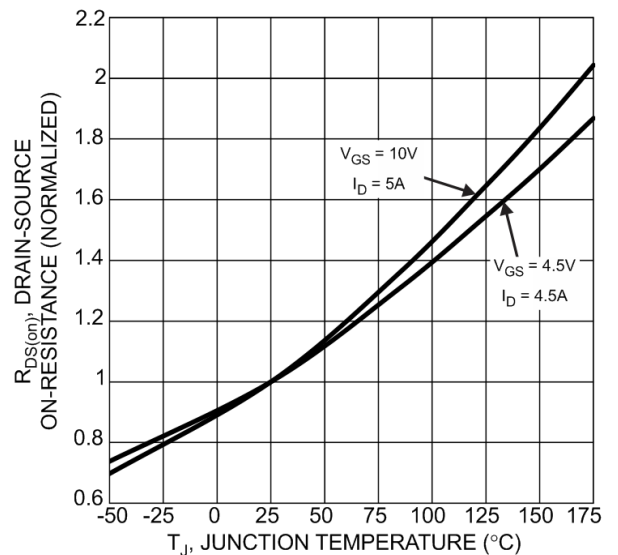
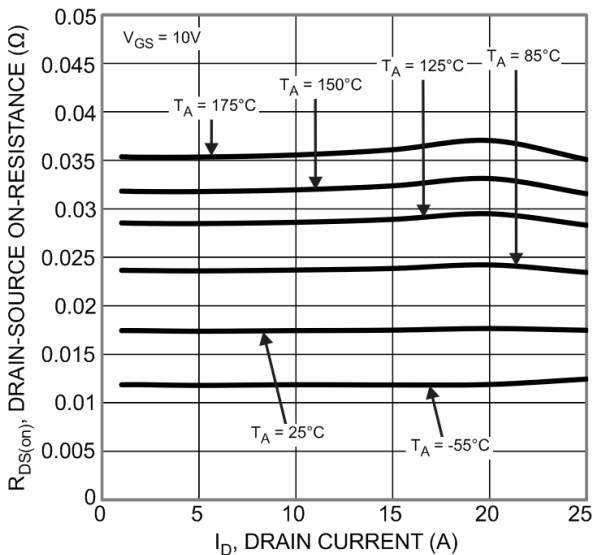
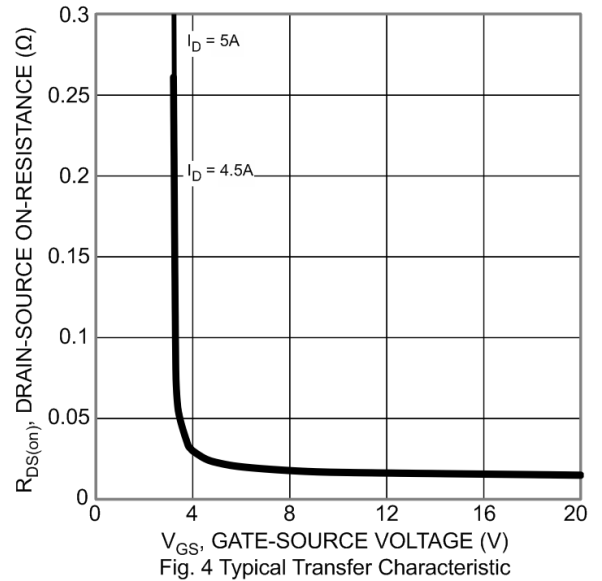
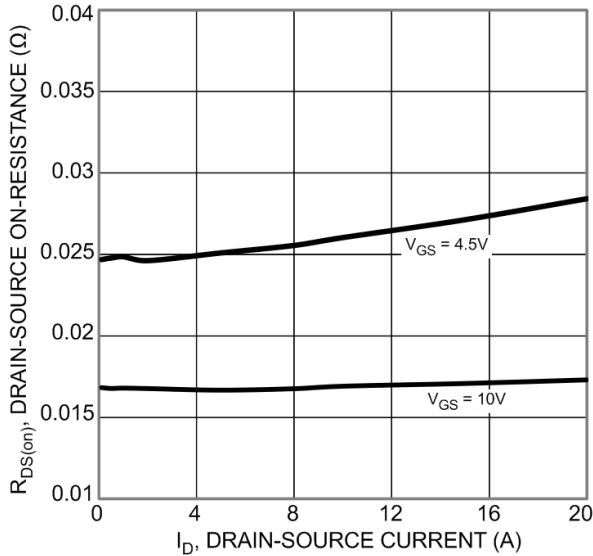
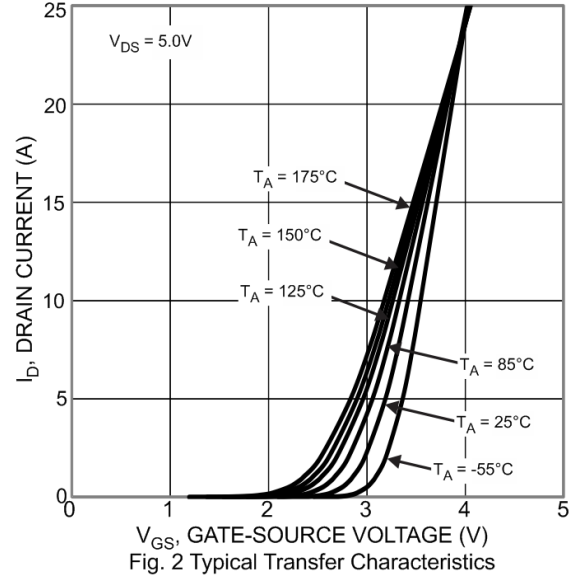
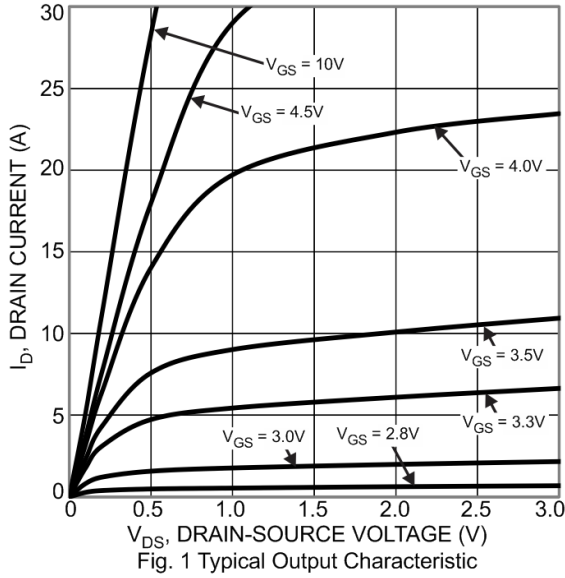
**Thermal Characteristics** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	98	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	3.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	42	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	4.0	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	17	25	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5A
		—	26	41		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	631	—	pF	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	200	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	19.5	—		
Gate Resistance	R <sub>g</sub>	—	1.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.4	—	nC	V <sub>DS</sub> = 40V, I <sub>D</sub> = 7.5A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	10.4	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.4	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.1	—	ns	V <sub>DD</sub> = 40V, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 2.7Ω, I <sub>D</sub> = 10A
Turn-On Rise Time	t <sub>r</sub>	—	9.7	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	18.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	8.6	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	28.5	—	ns	I <sub>F</sub> = 7.5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	21.7	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



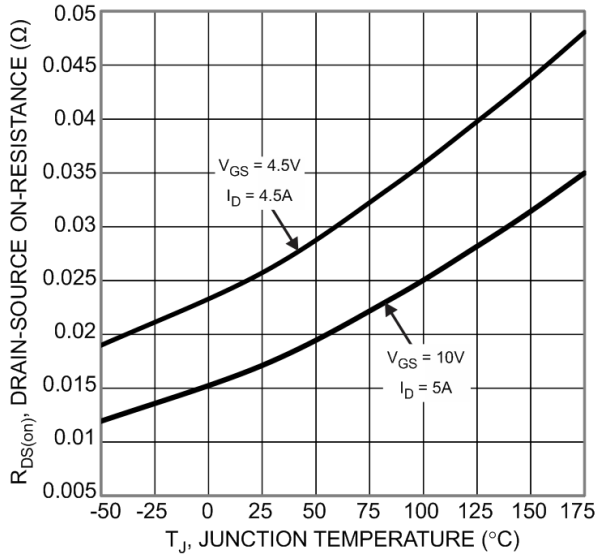


Fig. 7 On-Resistance Variation with Junction Temperature

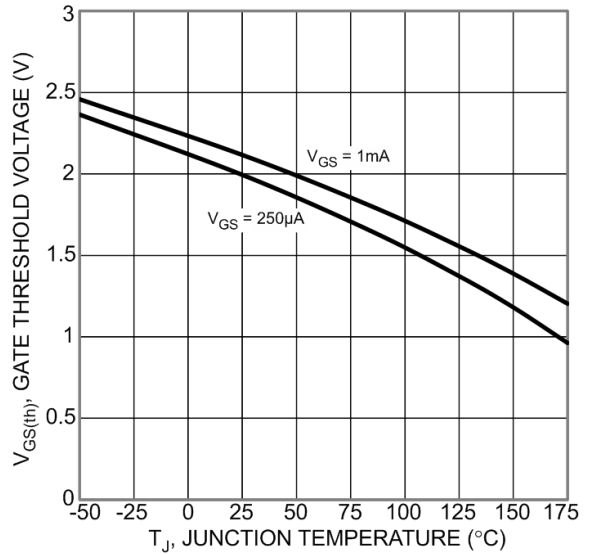


Fig. 8 Gate Threshold Variation vs Junction Temperature

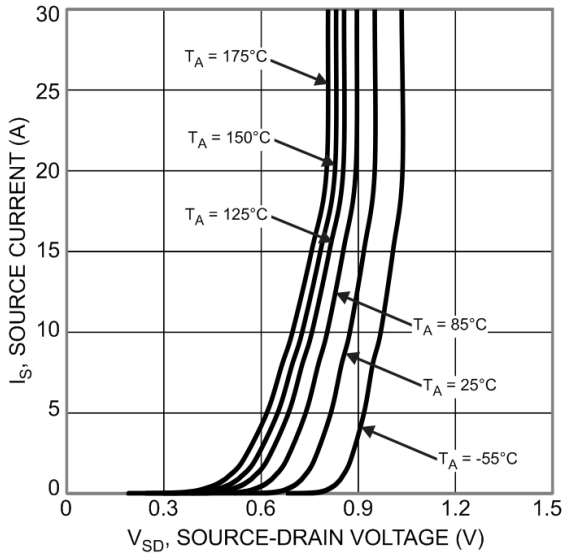


Fig. 9 Diode Forward Voltage vs Current

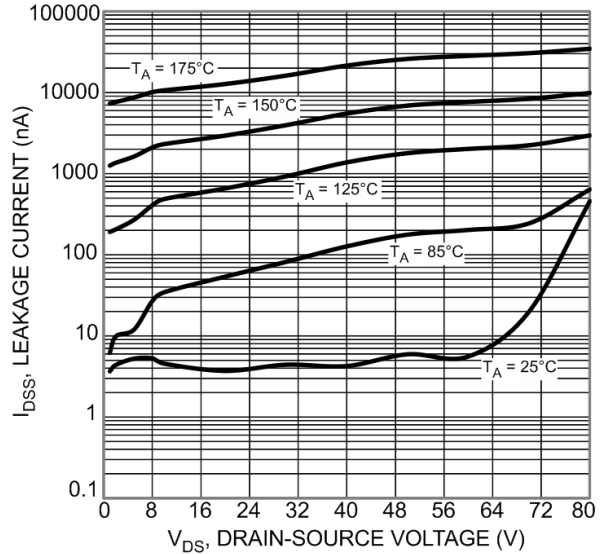


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

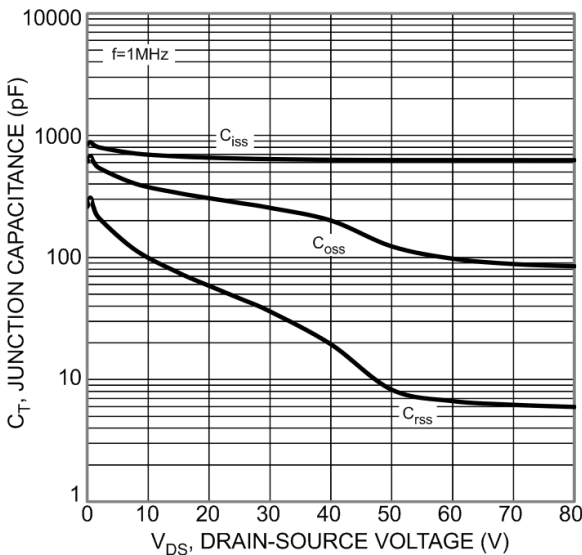


Fig. 11 Typical Junction Capacitance

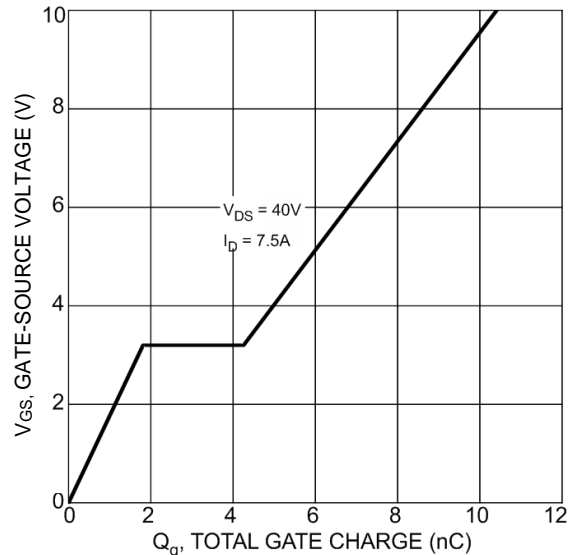
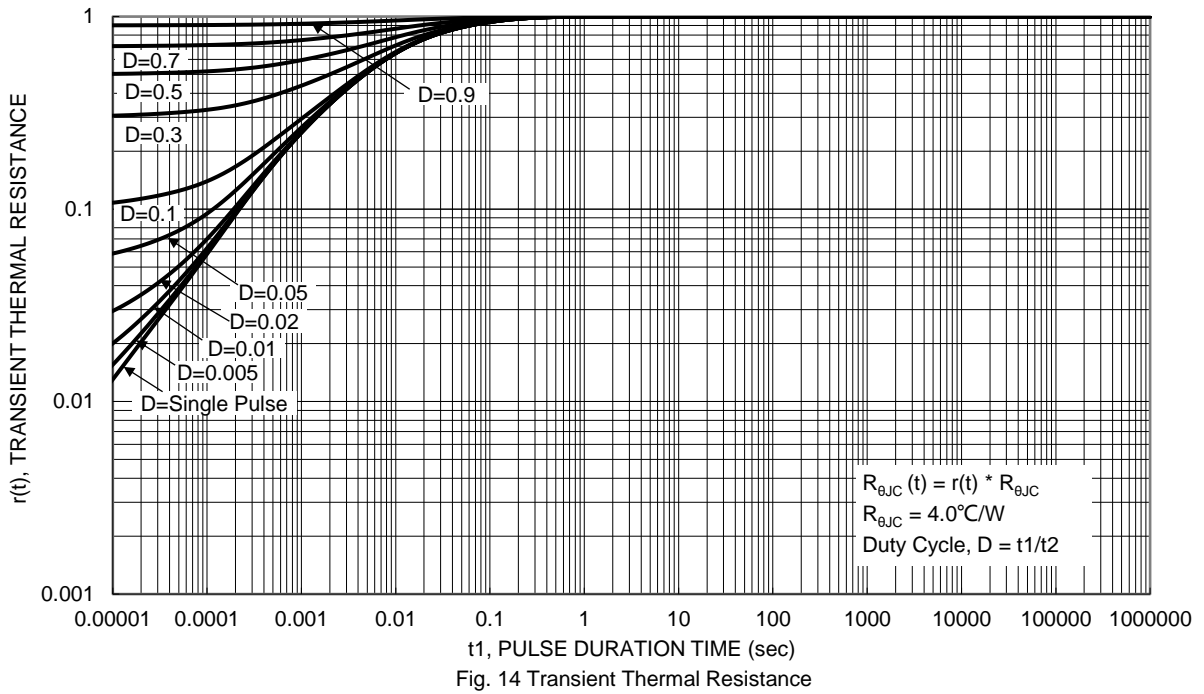
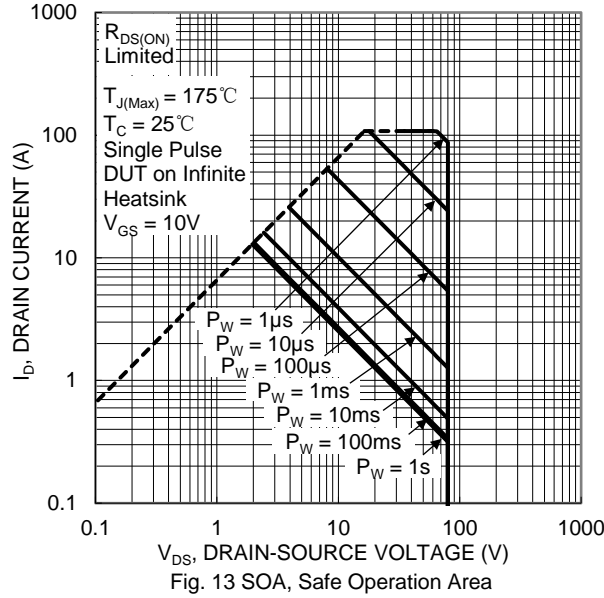


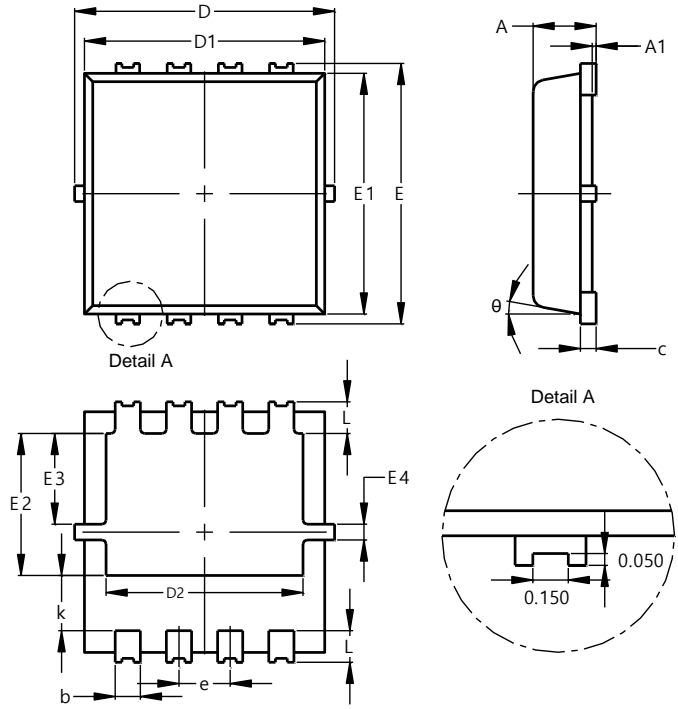
Fig. 12 Gate Charge



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (SWP) (Type UX)**

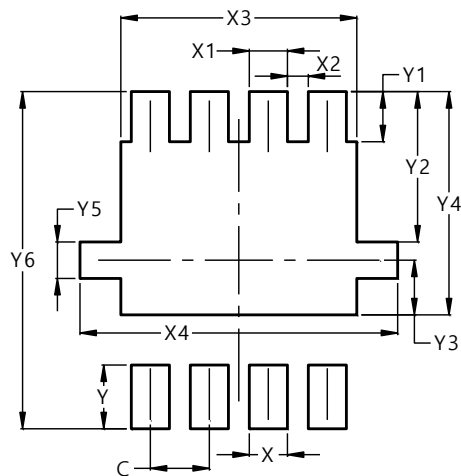


PowerDI3333-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (SWP) (Type UX)**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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